



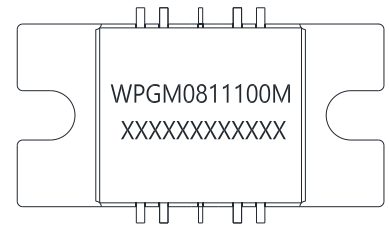
Product Features

- 8-11GHz GaN MMIC Power Amplifier
- Typical Small-signal Gain 29.5dB
- Typical Power Gain 24.7dB
- Typical Output Power 50.4dBm
- Typical PAE 38.7%
- 28V-32V operation

* Above Typical values measured at 9.5GHz and 32V

Applications

- General Purpose
- Communication System
- Radar System



Absolute Maximum Rating

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V _{DSS}	120	Volts	25°C
Gate-to-Source Voltage ³	V _{GS}	-10, +2	Volts	25°C
Storage Temperature ³	T _{STG}	-65, +150	°C	
Operating Junction Temperature ^{1,3}	T _J	225	°C	
Maximum Forward Gate Current ³	I _{GMAX}	10	mA	25°C
Maximum Drain Current ²	I _{DMAX}	1.04	A	I _d @ V _d =10V, V _g = 1V
Soldering Temperature ³	T _s	245	°C	

1. Continuous use at maximum temperature will affect MTTF.

2. Current limit for long term, reliable operation.

3. After additional updates.

Specifications (T_c=25°C, F₀=9.5GHz, V_{DD}=28V, I_{DQ}=573mA)

Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Small Signal Gain	G		26.9		dB	Pulse Width=100μsec, Duty Cycle=10%
Power Gain	G _P		22.5		dB	P _{sat} @ I _{gs} =1mA
Saturated Output Power	P _{OUT}		49.2		dBm	P _{sat} @ I _{gs} =1mA
Power Added Efficiency	PAE		36.8		%	P _{sat} @ I _{gs} =1mA

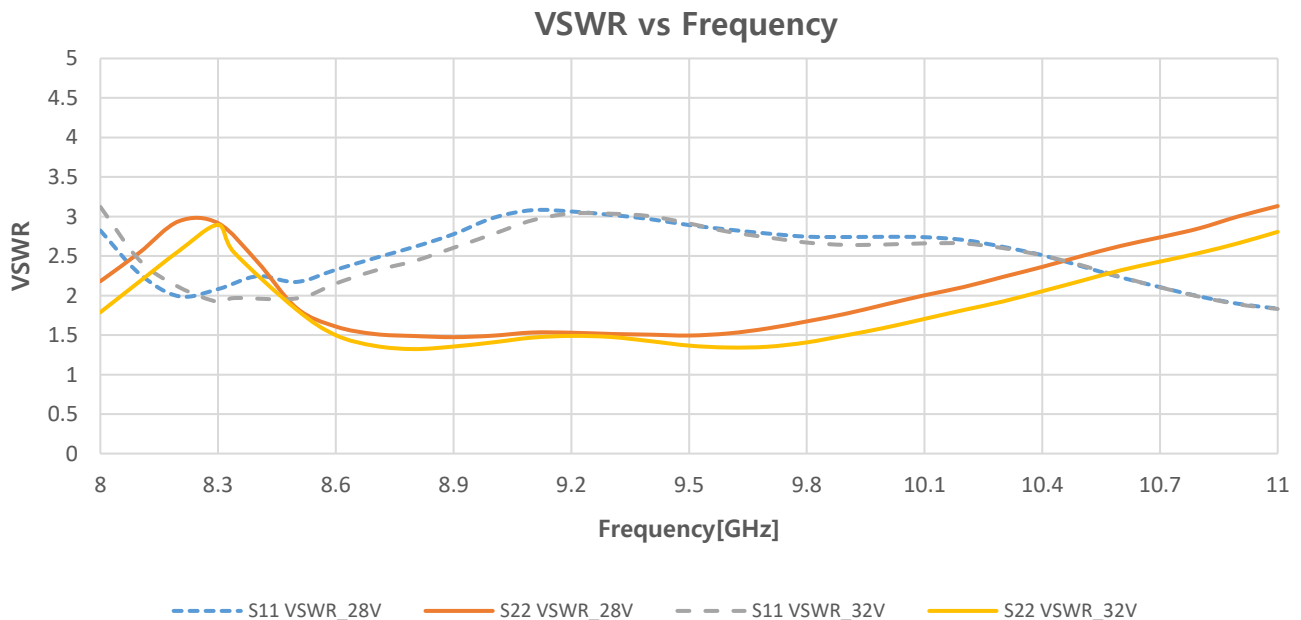
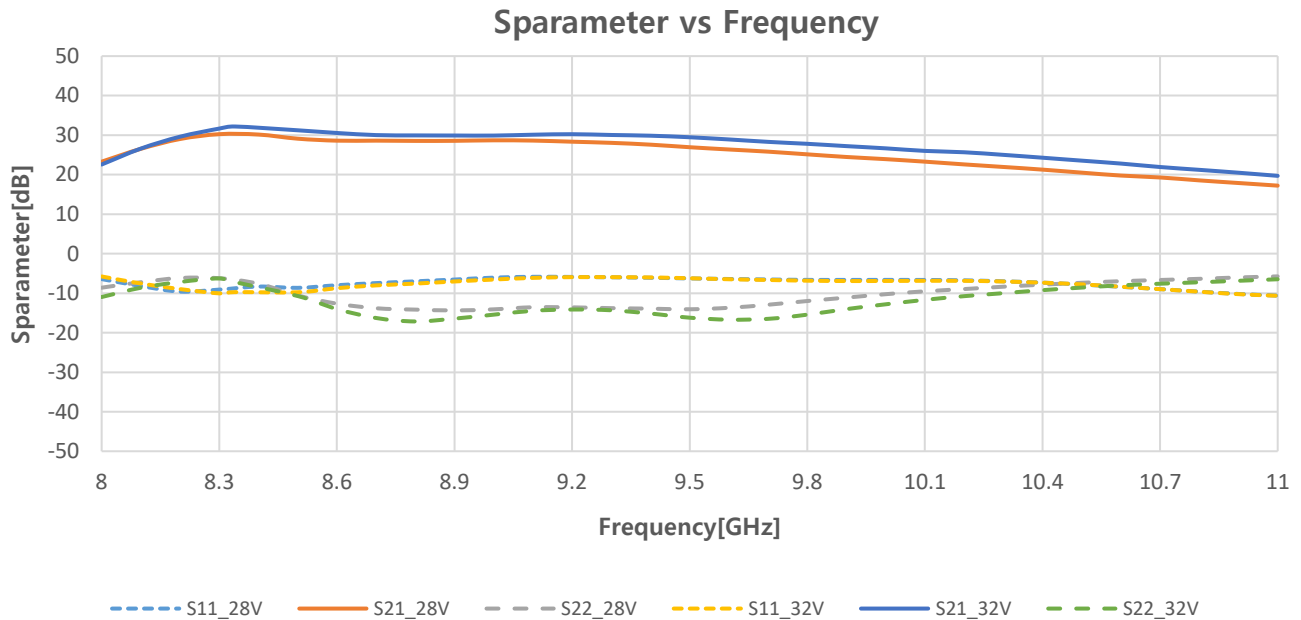
Specifications (T_c=25°C, F₀=9.5GHz, V_{DD}=32V, I_{DQ}=605mA)

Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Small Signal Gain	G		29.5		dB	Pulse Width=100μsec, Duty Cycle=10%
Power Gain	G _P		24.7		dB	P _{sat} @ I _{gs} =1mA
Saturated Output Power	P _{OUT}		50.4		dBm	P _{sat} @ I _{gs} =1mA
Power Added Efficiency	PAE		38.7		%	P _{sat} @ I _{gs} =1mA



Small-Signal Performance (Tc=25°C)

Drain Voltage= (28V IDQ=573mA), (32V IDQ=605mA)

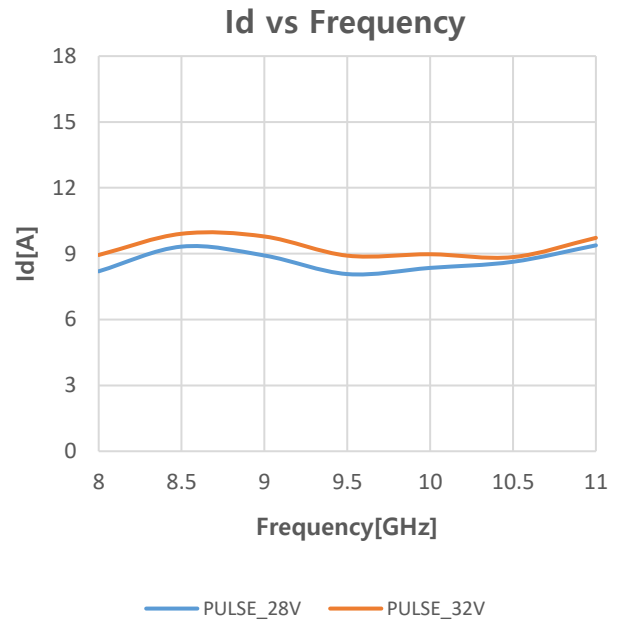
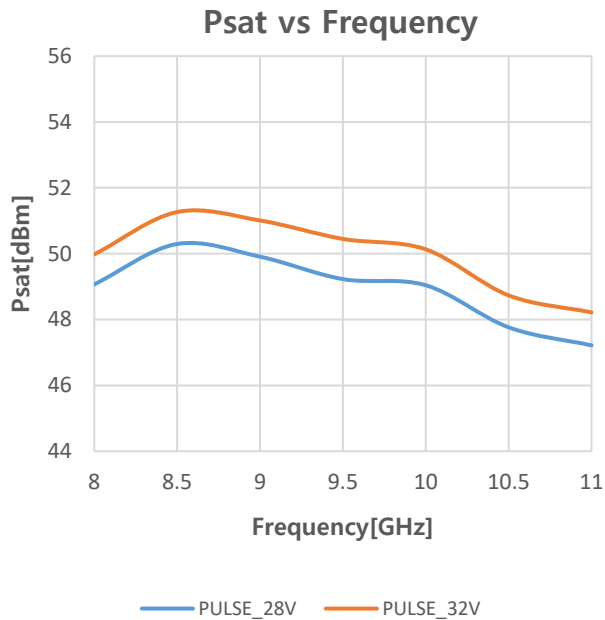




Psat, Id vs Frequency Performance (Tc=25°C)

Drain Voltage= (28V IDQ=573mA), (32V IDQ=605mA)

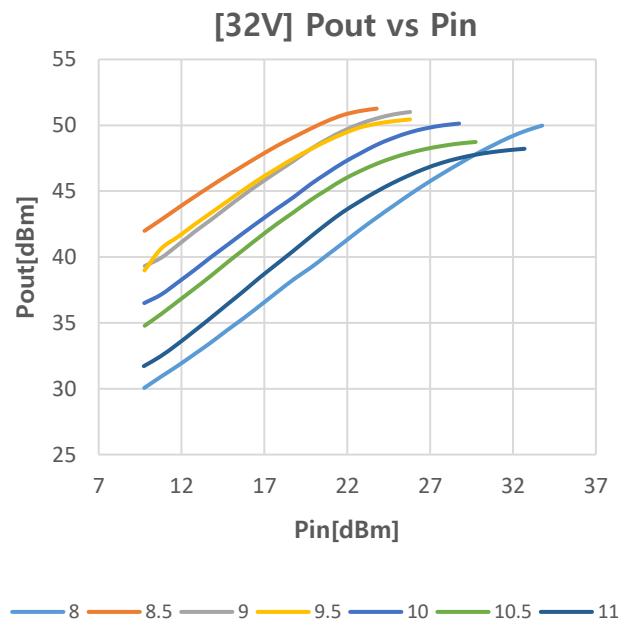
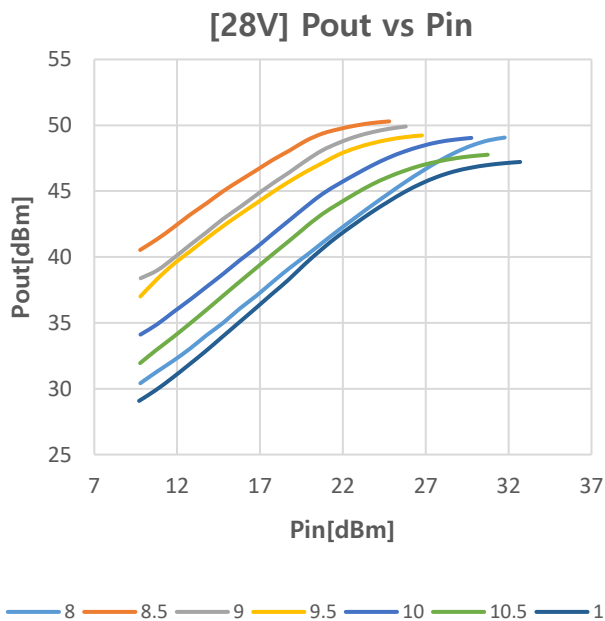
Pulse-Mode(Pulse Width=100μsec, Duty Cycle=10%)



Output Power (Pout) vs Input Power (Pin) Performance (Tc=25°C)

Drain Voltage= (28V IDQ=573mA), (32V IDQ=605mA)

Pulse-Mode(Pulse Width=100μsec, Duty Cycle=10%)

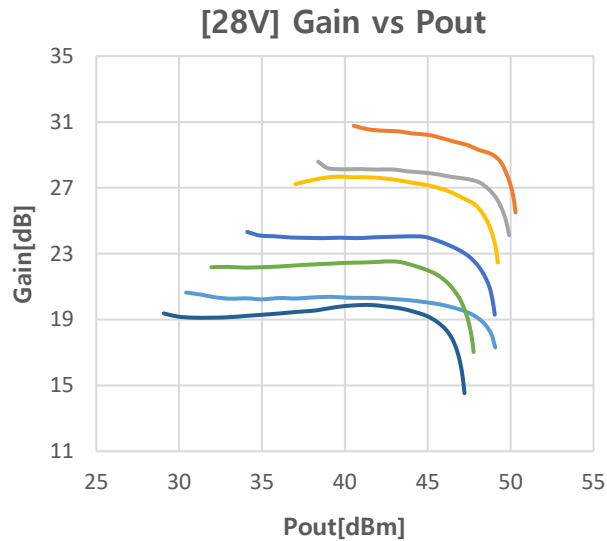




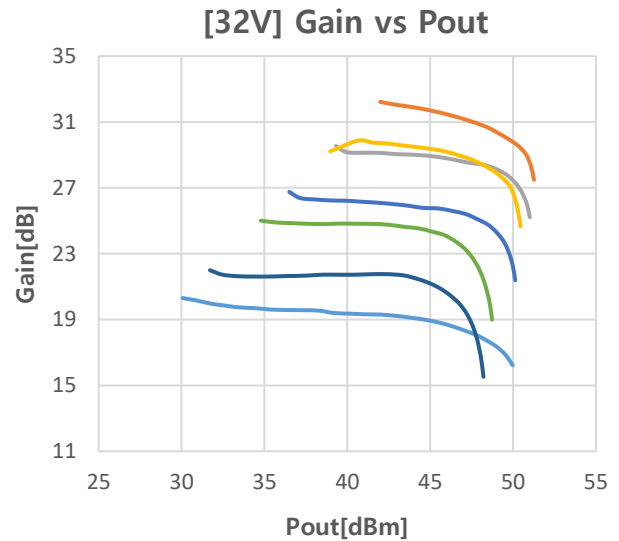
Gain vs Output Power (Pout) Performance (Tc=25°C)

Drain Voltage= (28V IDQ=573mA), (32V IDQ=605mA)

Pulse-Mode(Pulse Width=100μsec, Duty Cycle=10%)



8 8.5 9 9.5 10 10.5 11

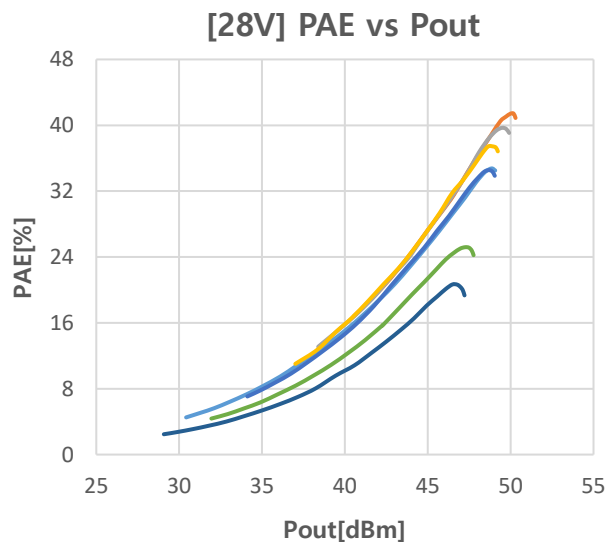


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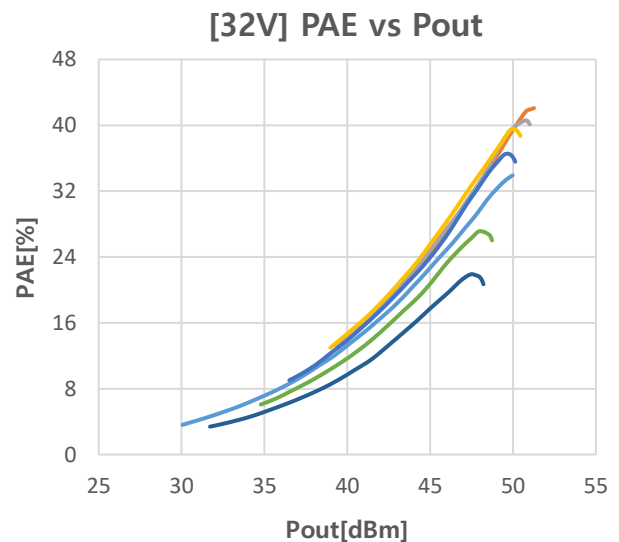
PAE vs Output Power (Pout) Performance (Tc=25°C)

Drain Voltage= (28V IDQ=573mA), (32V IDQ=605mA)

Pulse-Mode(Pulse Width=100μsec, Duty Cycle=10%)



8 8.5 9 9.5 10 10.5 11

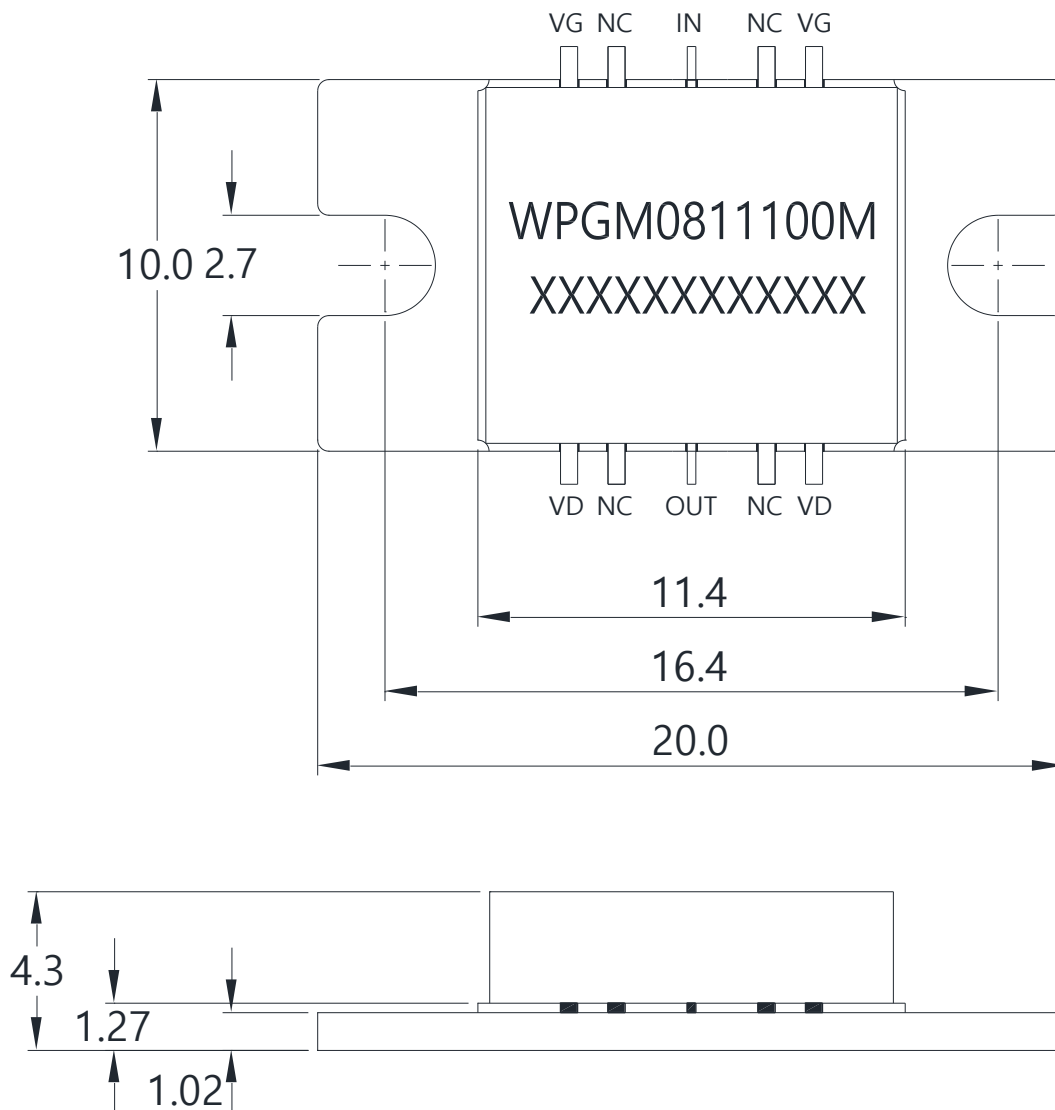


8 8.5 9 9.5 10 10.5 11



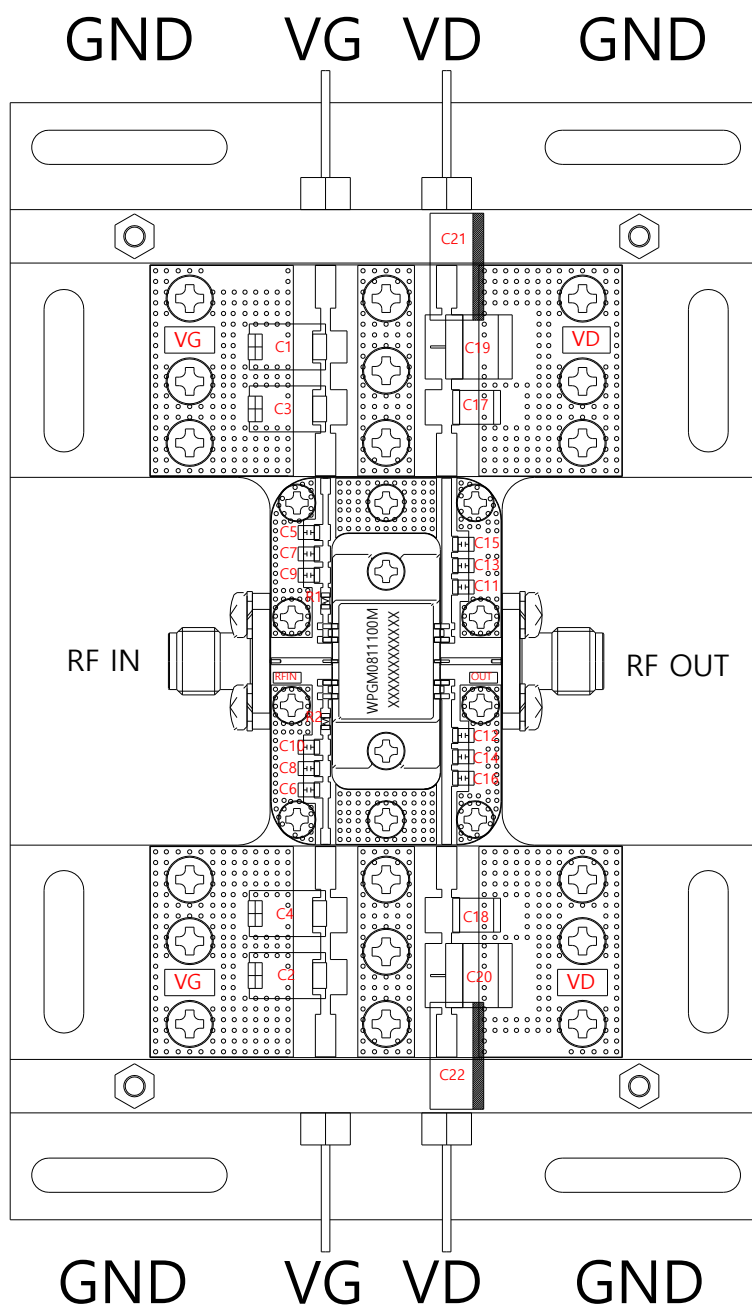
Product Dimension

- Product Type: MPKG, 10-lead bolt-down
- Unit: mm





Evaluation Board Circuit Outline





Bias Sequence

1. VG connection must be biased from both sides.
2. VD connection must be biased from both sides.
3. VG bias must be applied before VD

Test Condition

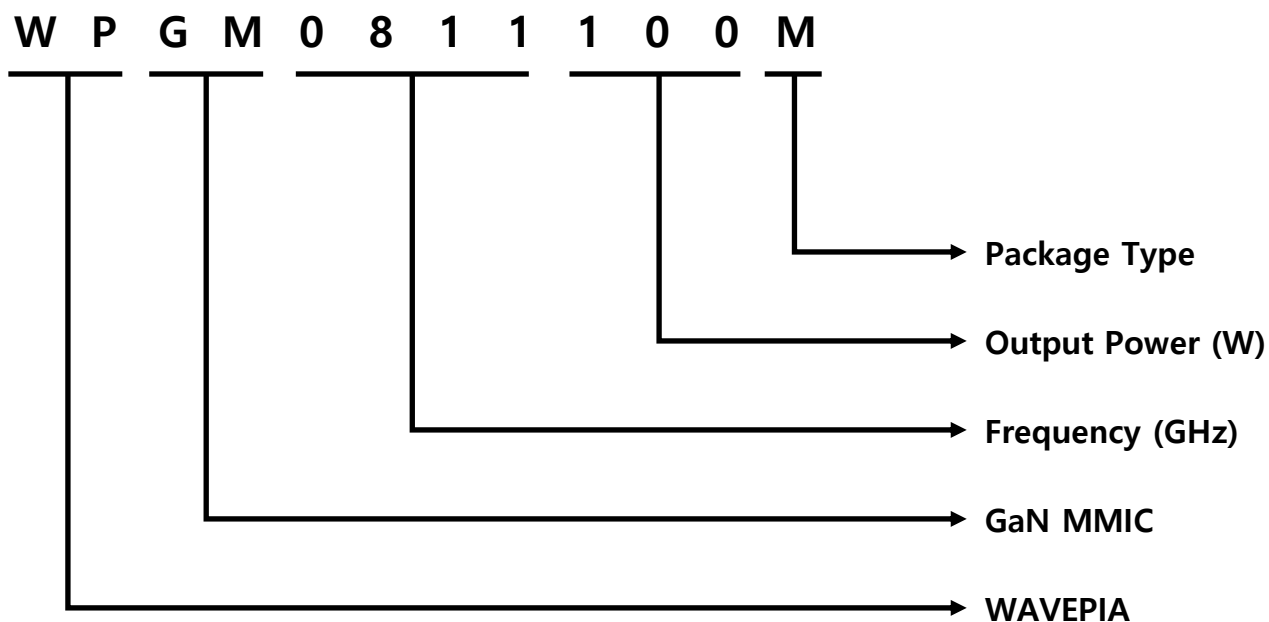
1. VD=28V, IDQ=573mA, VG=-2.51V
2. VD=32V, IDQ=605mA, VG=-2.51V

Evaluation Board Circuit Bill of Materials

Reference	Part Number	Value	Description	Package	Manufacturer	EA
C1, C2	293D476X9016D2TE3	47uF / 16V	Tantalium Capacitor	2917	MICRO TECHNOLOGY	2
C3, C4	TAJD106K035RNJ	10uF / 35V	Tantalium Capacitor	2917	KYOCERA AVX	2
C17, C18	CGA8N3X7R2E474K230KA	470nF / 250V	Ceramic Capacitor	1812	TDK	2
C19, C20	22201C106KAT2A	10uF / 100V	Ceramic Capacitor	2020	KYOCERA AVX	2
C5, C6, C15, C16	C2012X7S2A474K125AB	470nF / 100V	Ceramic Capacitor	0805	TDK	4
C7, C8, C13, C14	CL21B103KCANNNC	10nF / 100V	Ceramic Capacitor	0805	SAMSUNG	4
C9, C10, C11, C12	251R15S101JV4E	100pF / 250V	Ceramic Capacitor	0805	JOHANSON	4
R1, R2	WR06X100 JTL	10ohm	Chip Resistor	0603	WALSIN	2
C21, C22	KMG 50V 47uF MAX	E-Cap (Dip Type)	electrolytic capacitor	0603	SAMYOUNG	2
J1, J2	SM06FS064	SMA / 4 Hole	SMA_4 Hole (DC to 26.5 GHz)	-	WITHWAVE	2
P1	-	-	RO4003C 12mil	-	Rogers	1
P2	-	-	RO4003C 12mil	-	Rogers	2
Q1	WPGM0811100M	-	GaN MMIC	-	WAVEPIA	1



Part Number System



Parameter	Value	Units
Lower Frequency	8	GHz
Upper Frequency	11	GHz
Output Power	100	W
Transistor Type	GaN MMIC	-
Package	MPKG	-



Handling Precautions

Parameter	Classification	Standard
ESD - Human Body Model (HBM)	Class 1A	ANSI/ESDA/JEDEC JS-001-2017
ESD - Charge Device Model (CDM)	Class C2	ANSI/ESDA/JEDEC JS-002-2018
MSL - Moisture Sensitivity Level	N/A	



ATTENTION
Electrostatic
Sensitive Device

Contact Information

For the latest specifications, additional product information, worldwide sales and distribution locations:

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Email : sales@wavepia.com

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